



STW10NC60 STH10NC60FI

N-CHANNEL 600V - 0.6Ω - 10A - TO-247/ISOWATT218

PowerMesh™ II MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW10NC60	600 V	< 0.75 Ω	10 A
STH10NC60FI	600 V	< 0.75 Ω	10 A (*)

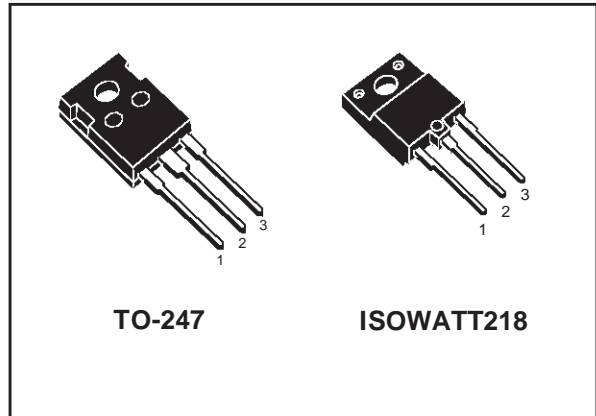
- TYPICAL R_{DS(on)} = 0.6 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

DESCRIPTION

The PowerMESH™ II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron*area figure of merit while keeping the device at the leading edge for what concerns switching speed, gate charge and ruggedness.

APPLICATIONS

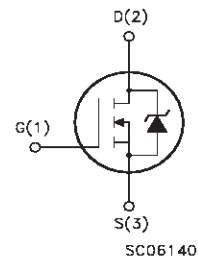
- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVER



TO-247

ISOWATT218

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW10NC60	STH10NC60FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	600		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	600		V
V _{GS}	Gate- source Voltage	±30		V
I _D	Drain Current (continuous) at T _C = 25°C	10	10 (*)	A
I _D	Drain Current (continuous) at T _C = 100°C	6.3	6.3 (*)	A
I _{DM} (1)	Drain Current (pulsed)	40	40 (*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	160	60	W
	Derating Factor	1.28	0.48	W/°C
dv/dt	Peak Diode Recovery voltage slope	3.5		V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	-	2500	V
T _{stg}	Storage Temperature	- 55 to 150		°C
T _j	Max. Operating Junction Temperature			

(*) Pulse width limited by safe operating area

(1) I_{SD} ≤ 10A, di/dt ≤ 100A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

(*) Limited only by Maximum Temperature Allowed

STW10NC60 / STH10NC60FI

THERMAL DATA

		TO-247	ISOWATT218	
Rthj-case	Thermal Resistance Junction-case Max	0.78	2.08	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	10	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	820	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	600			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 50	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 4.5 A		0.6	0.75	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} = 20 V, I _D = 4.5A		9		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1420		pF
C _{oss}	Output Capacitance			205		pF
C _{rss}	Reverse Transfer Capacitance			35		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 300V, I_D = 4.5 A$ $R_G = 4.7\Omega, V_{GS} = 10V$		20		ns
t_r	Rise Time	(see test circuit, Figure 3)		16		ns
Q_g	Total Gate Charge	$V_{DD} = 480V, I_D = 9.0 A,$ $V_{GS} = 10V$		55	77	nC
Q_{gs}	Gate-Source Charge			4.5		nC
Q_{gd}	Gate-Drain Charge			31		nC

SWITCHING OFF

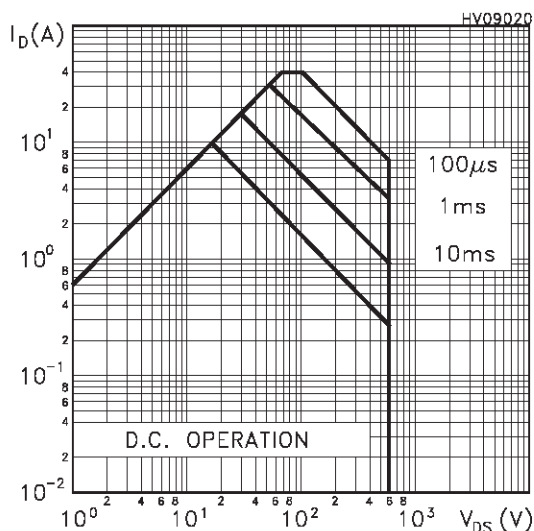
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 300 V, I_D = 4.5 A$ $R_G = 4.7\Omega, V_{GS} = 10 V$ (Resistive Load see, Figure 3)		64		ns
t_f	Fall Time			32		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 480V, I_D = 9.0 A,$ $R_G = 4.7\Omega, V_{GS} = 10V$		19		ns
t_f	Fall Time	(Inductive Load see, Figure 5)		13		ns
t_c	Cross-over Time			32		ns

SOURCE DRAIN DIODE

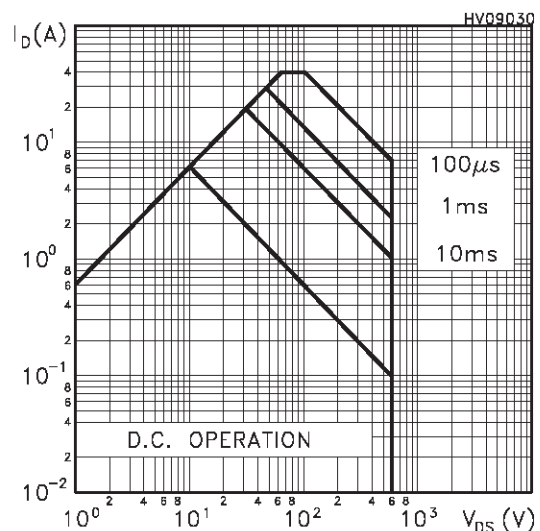
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				10	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				40	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 9 A, V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 9 A, di/dt = 100A/\mu s,$ $V_{DD} = 100V, T_j = 150^\circ C$		600		ns
Q_{rr}	Reverse Recovery Charge	(see test circuit, Figure 5)		4.7		μC
I_{RRM}	Reverse Recovery Current			15.5		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

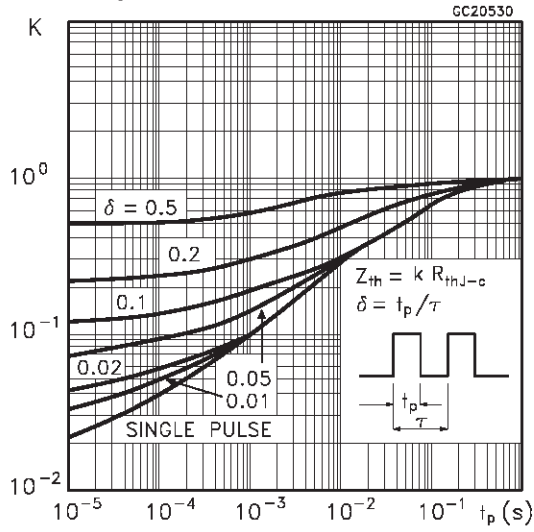
Safe Operating Area for TO-247



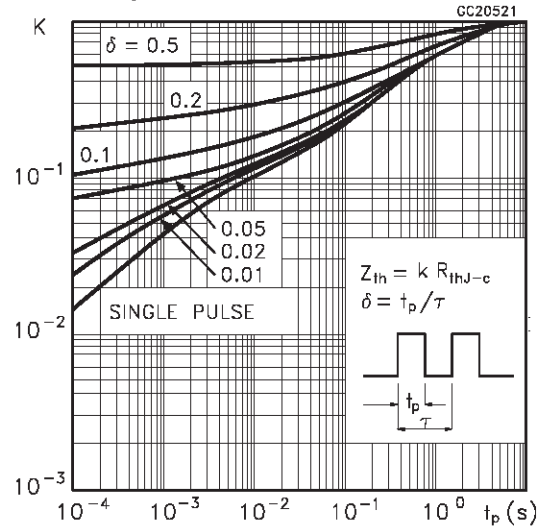
Safe Operating Area for ISOWATT218



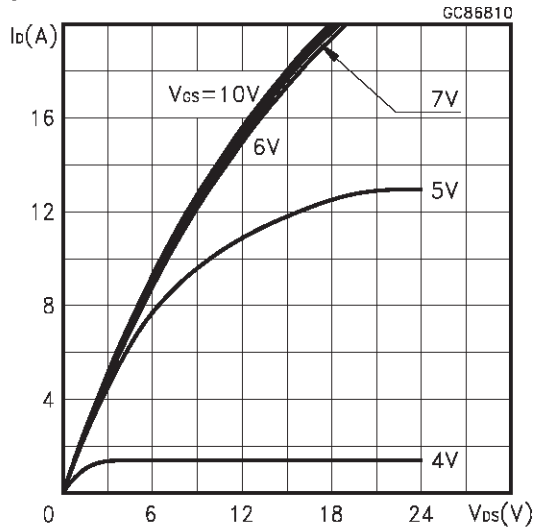
Thermal Impedance for TO-247



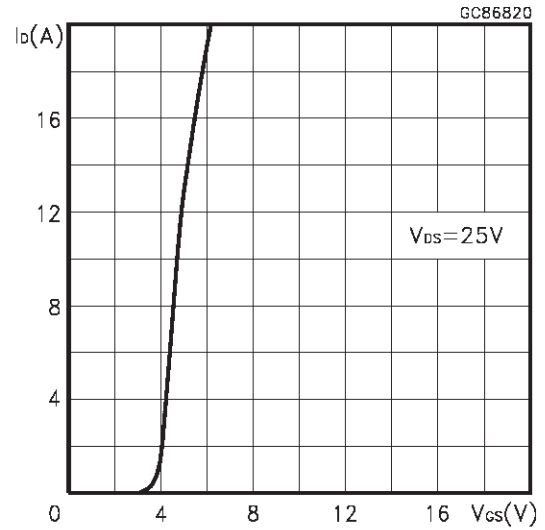
Thermal Impedance for ISOWATT218



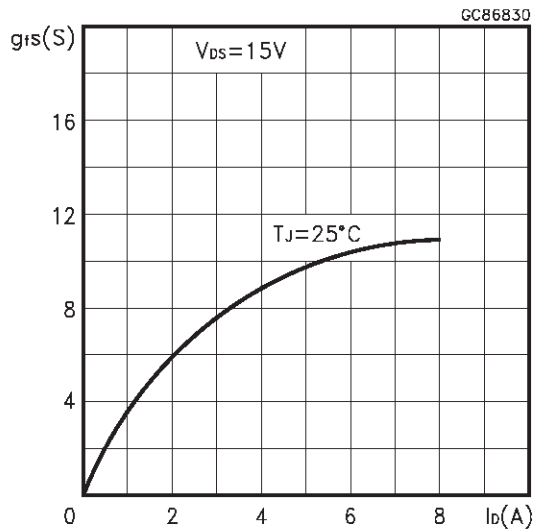
Output Characteristics



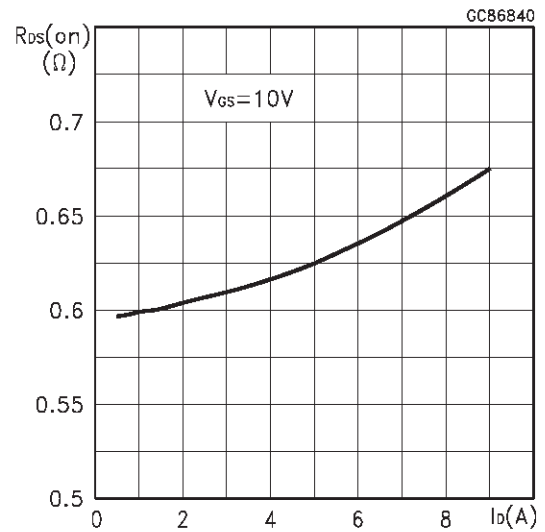
Transfer Characteristics



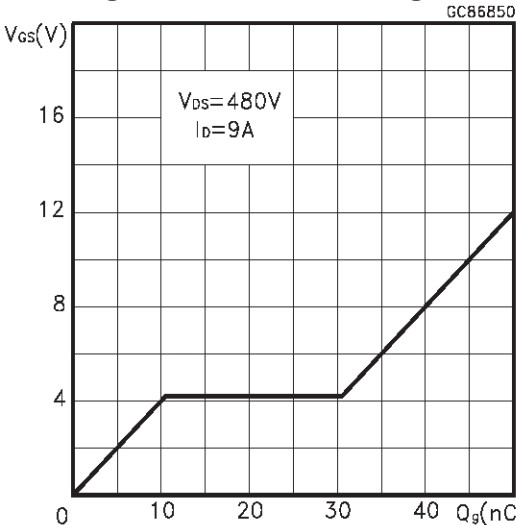
Transconductance



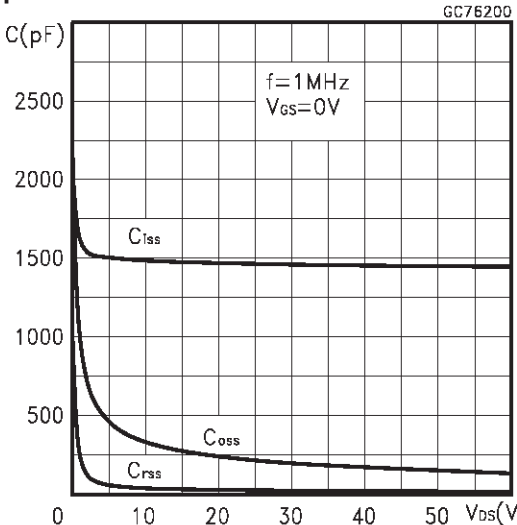
Static Drain-source On Resistance



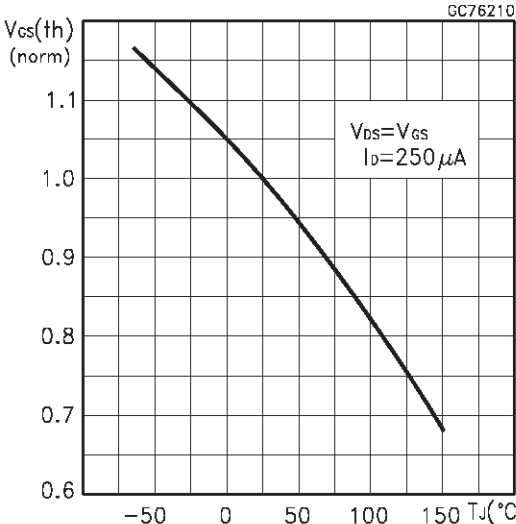
Gate Charge vs Gate-source Voltage



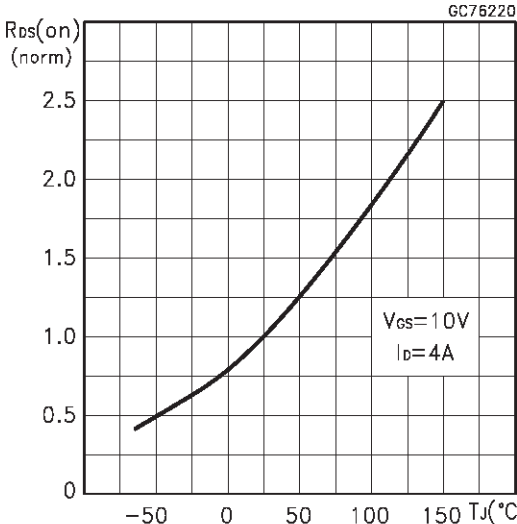
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

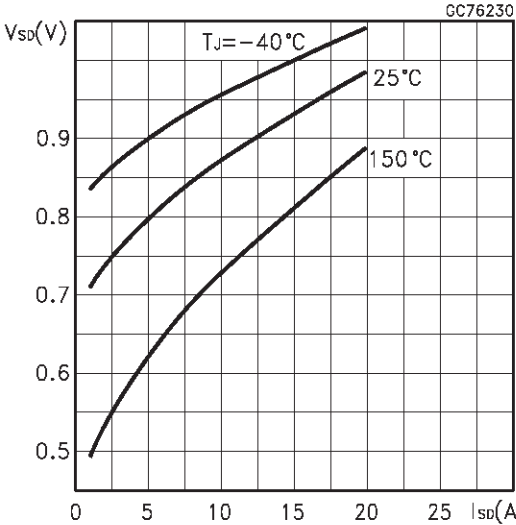


Fig. 1: Unclamped Inductive Load Test Circuit

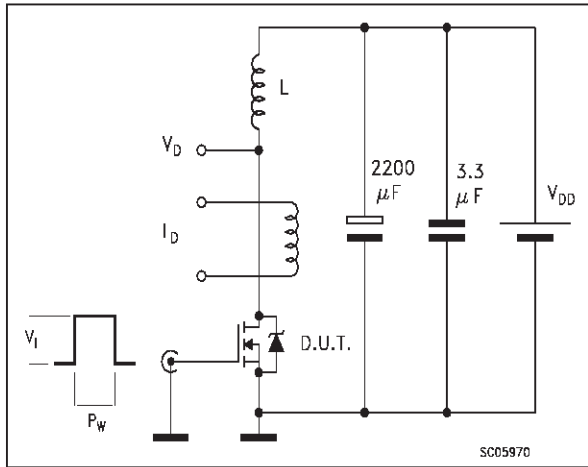


Fig. 2: Unclamped Inductive Waveform

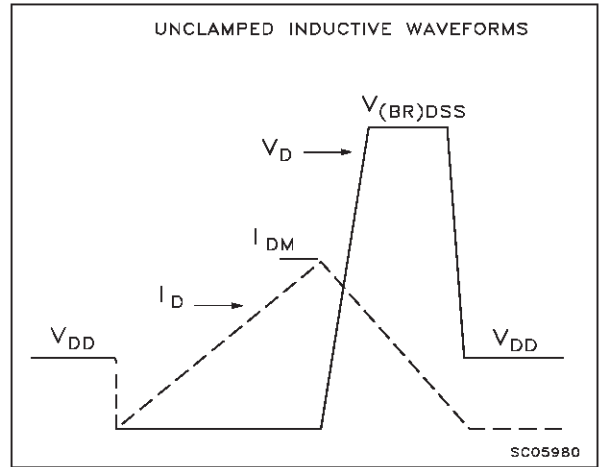


Fig. 3: Switching Times Test Circuit For Resistive Load

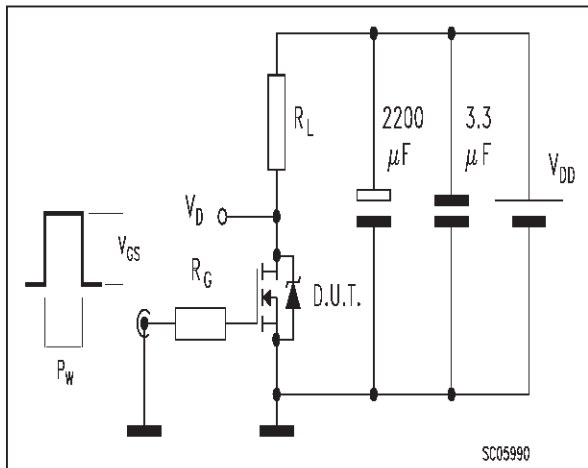


Fig. 4: Gate Charge test Circuit

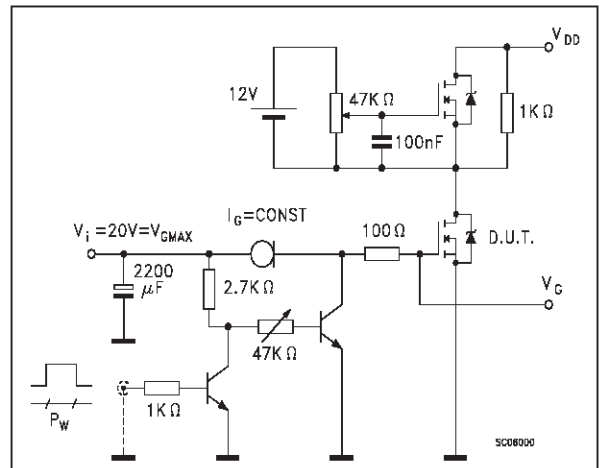
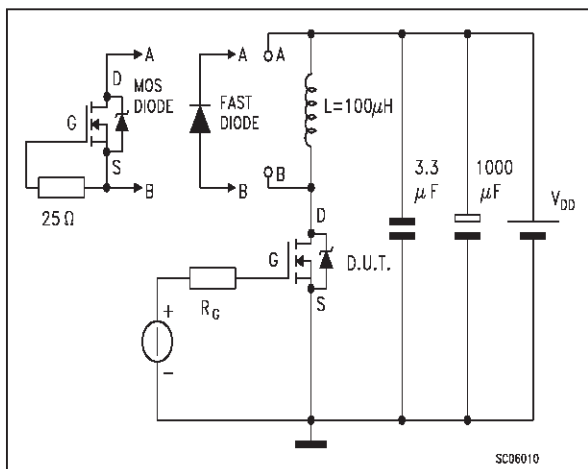
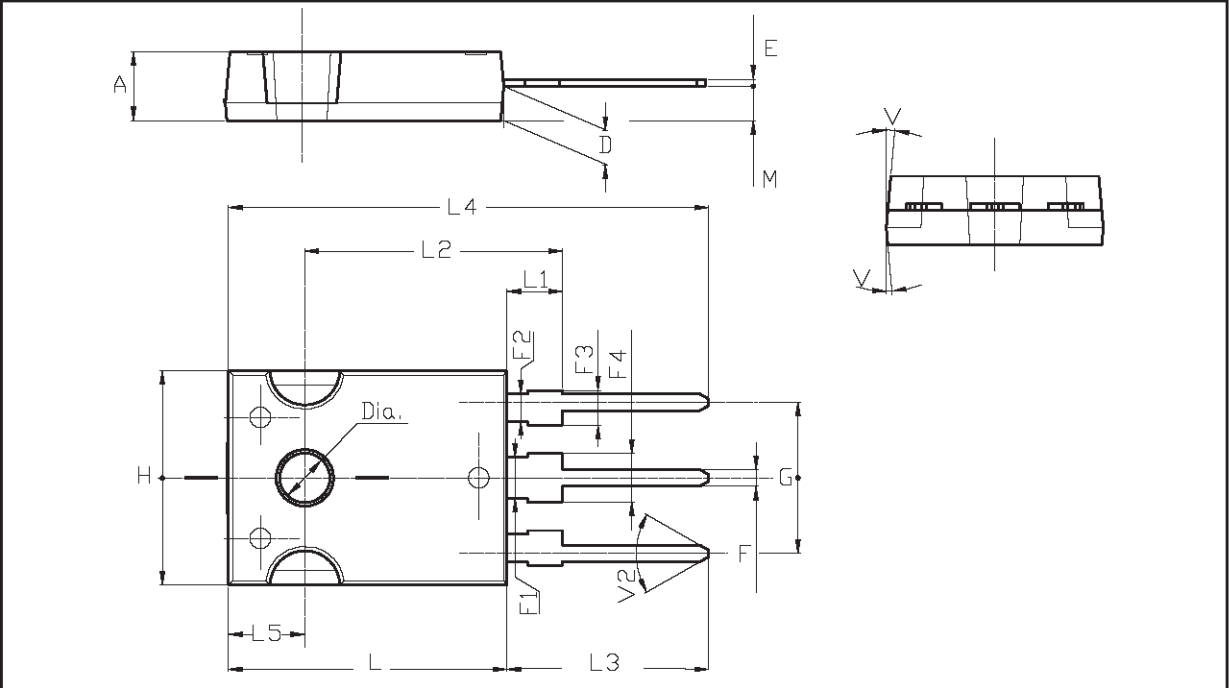


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



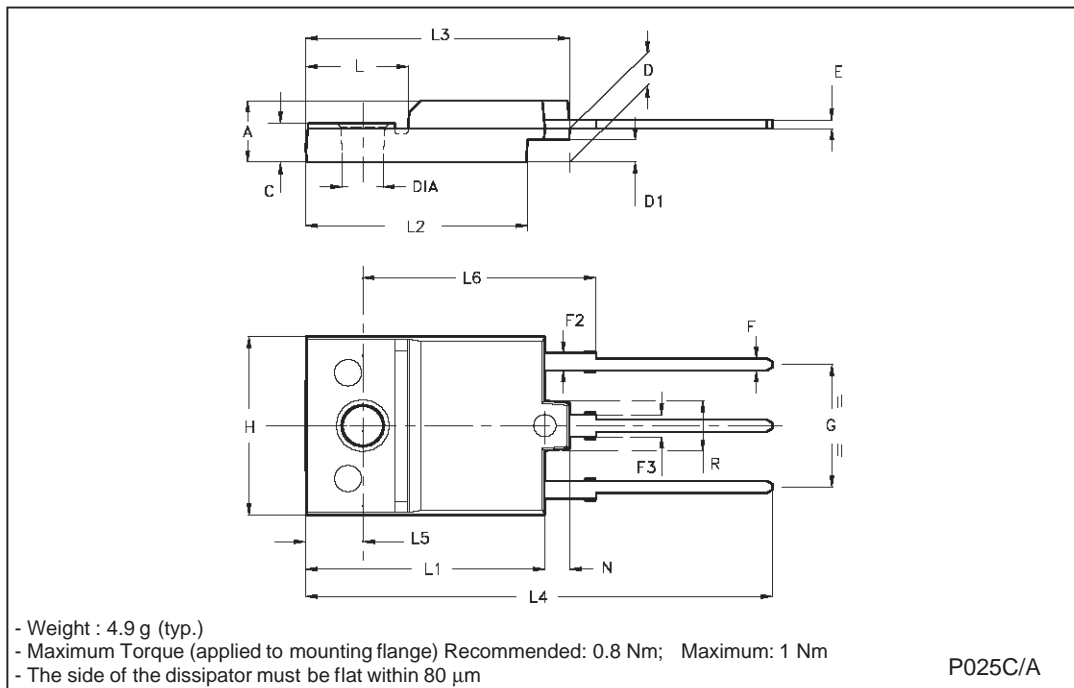
TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
D	2.20		2.60	0.08		0.10
E	0.40		0.80	0.015		0.03
F	1		1.40	0.04		0.05
F1		3			0.11	
F2		2			0.07	
F3	2		2.40	0.07		0.09
F4	3		3.40	0.11		0.13
G		10.90			0.43	
H	15.45		15.75	0.60		0.62
L	19.85		20.15	0.78		0.79
L1	3.70		4.30	0.14		0.17
L2		18.50			0.72	
L3	14.20		14.80	0.56		0.58
L4		34.60			1.36	
L5		5.50			0.21	
M	2		3	0.07		0.11
V		5°			5°	
V2		60°			60°	
Dia	3.55		3.65	0.14		0.143



ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.211		0.222
C	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	1.05		1.25	0.041		0.049
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
G	10.80		11.20	0.425		0.441
H	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2001 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco -
Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

<http://www.st.com>